

FIG. 1A

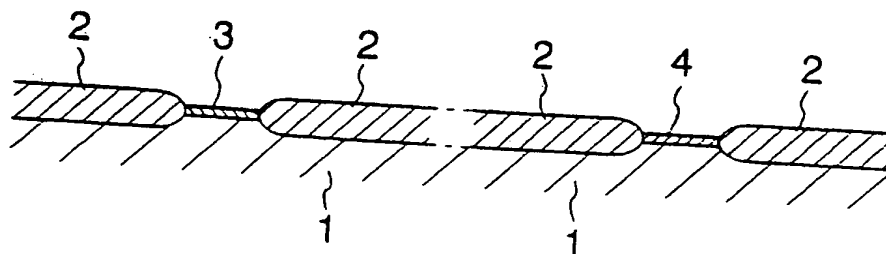


FIG. 1B

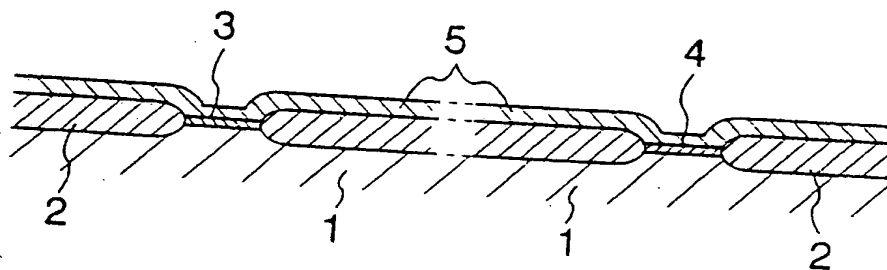


FIG. 1C

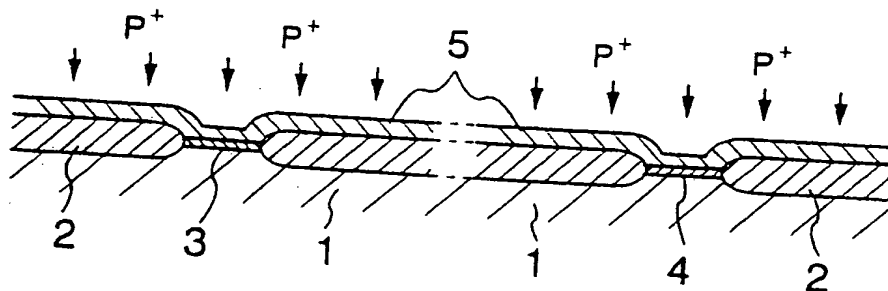


FIG. 1D

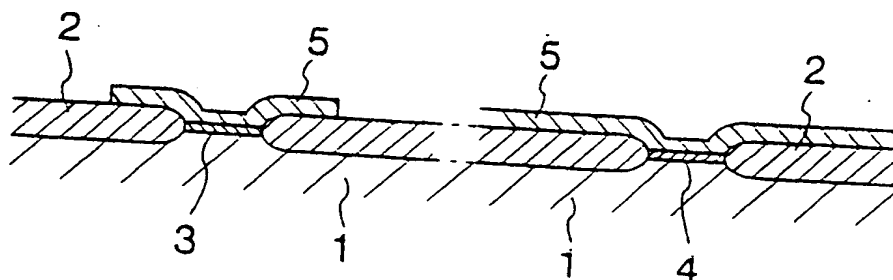


FIG. 1E

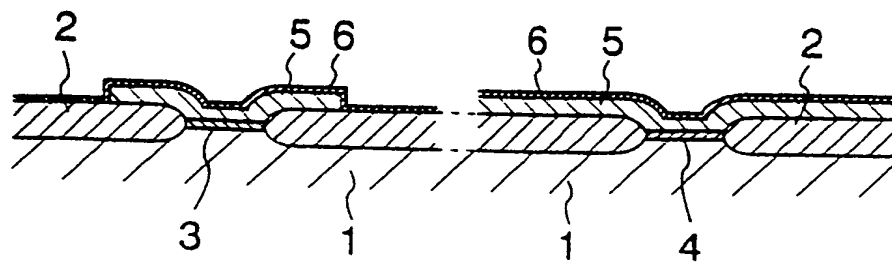


FIG. 1F

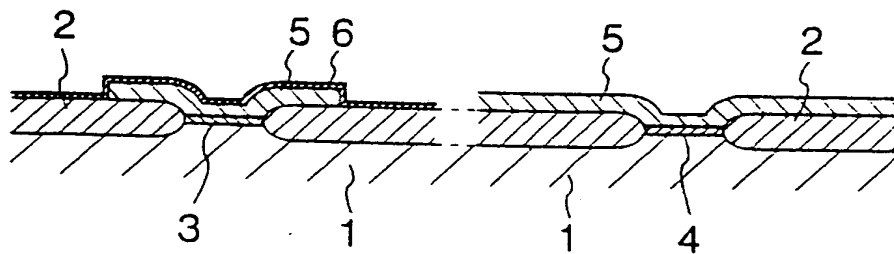


FIG. 1G

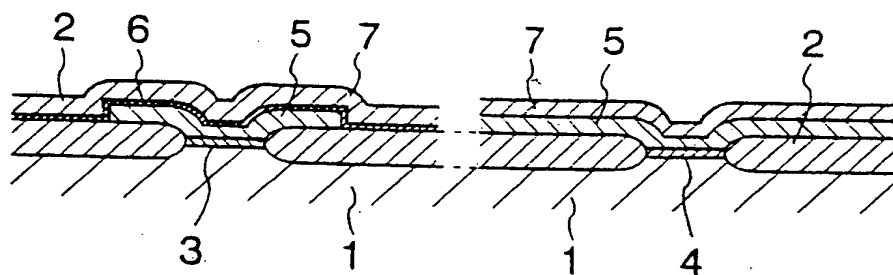


FIG. 1H

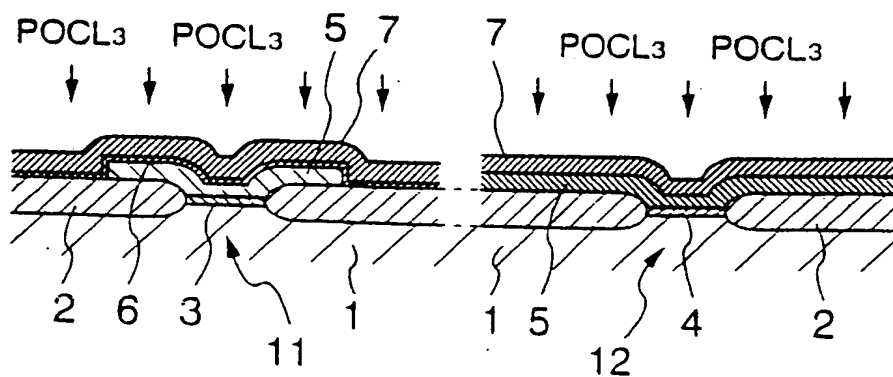


FIG. 2A

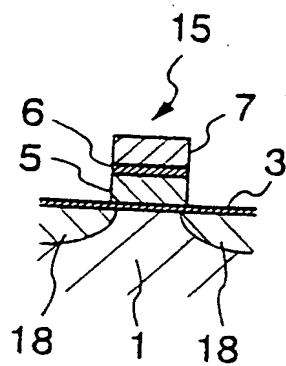
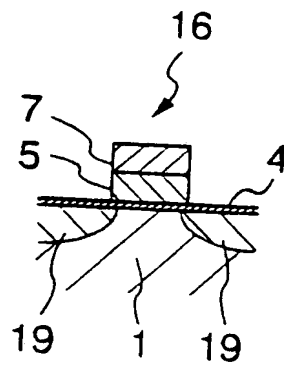


FIG. 2B



A cross-sectional view of a semiconductor device. A central vertical protrusion (27) is located on a substrate (26). The protrusion has a top surface (28) and a side surface (27). The substrate (26) is shown in cross-section with a hatched pattern. A layer (5) is formed on the substrate, and a layer (7) is formed on top of layer (5). A layer (6) is formed on the side surface of the protrusion (27). A layer (4) is formed on the substrate (26) and is connected to the side surface of the protrusion (27). A layer (2) is formed on the substrate (26) and is connected to the side surface of the protrusion (27). A layer (12) is formed on the substrate (26) and is connected to the side surface of the protrusion (27).